

SDURB860 ULTRAFAST PLASTIC RECTIFIER

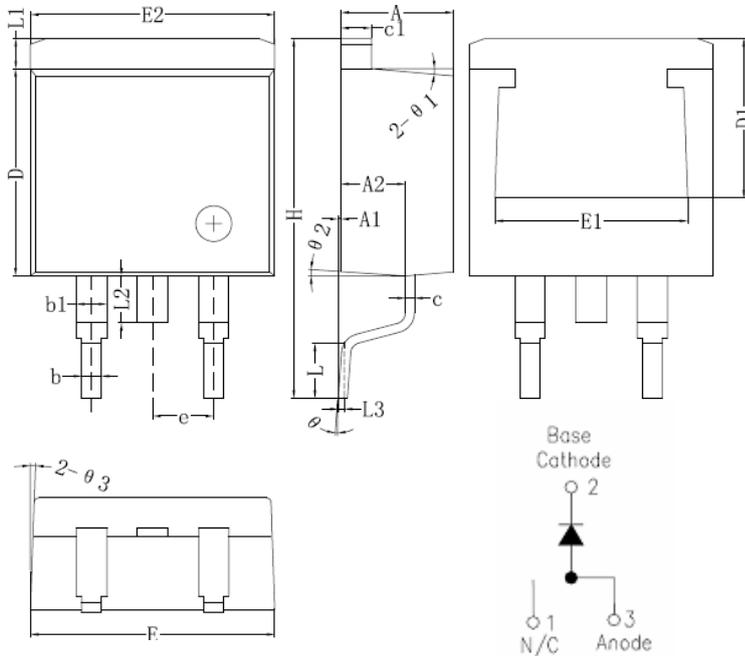
Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Features:

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

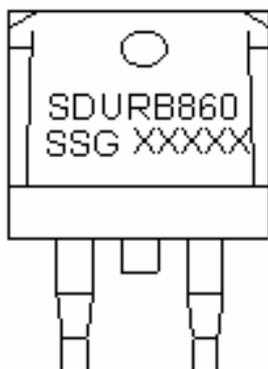
Mechanical Dimensions: In mm /Inches



D² PAK

Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

Marking Diagram:



Where XXXXX is YYWWL

SDUR = Device Type
B = Package type
8 = Forward Current (8A)
60 = Reverse Voltage (600V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SDURB860	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	600	V
Max. Average Forward	I _{F (AV)}	50% duty cycle @Tc=100°C, rectangular wave form	8	A
Max. Peak One Cycle Non-Repetitive Surge Current (Per leg)	I _{FSM}	8.3ms, Half Sine pulse	110	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 8A, Pulse, $T_J = 25^\circ\text{C}$	1.35	1.7	V
Max. Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	0.2	8	μA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	0.15	1	mA
Max. Reverse Recovery Time	t_{rr}	$I_F=500\text{mA}$, $I_R=1\text{A}$, and $I_{rm}=250\text{mA}$, $T_J = 25^\circ\text{C}$	45	50	ns

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	25	K/W
Approximate Weight	wt	-	1.85	g
Case Style	D ² PAK			

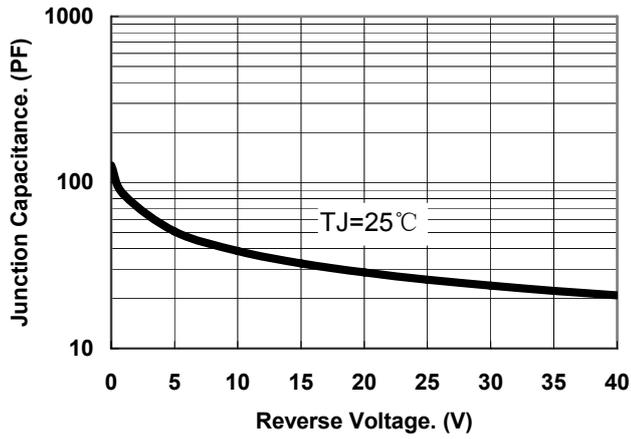


Fig.1-Typical Junction Capacitance

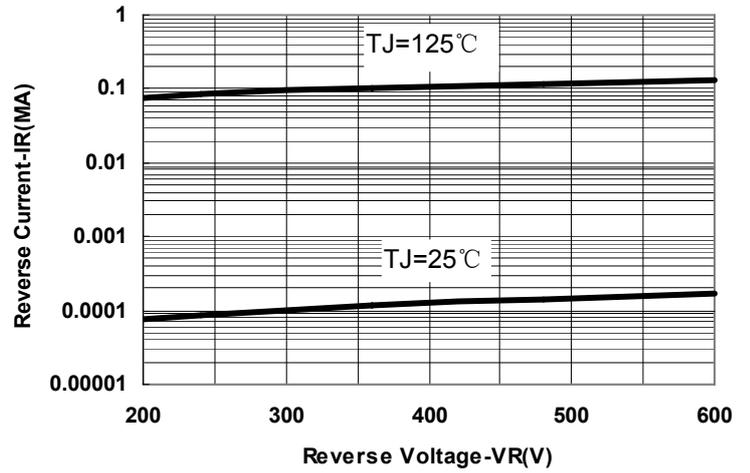


Fig.2-Typical Reverse Characteristics

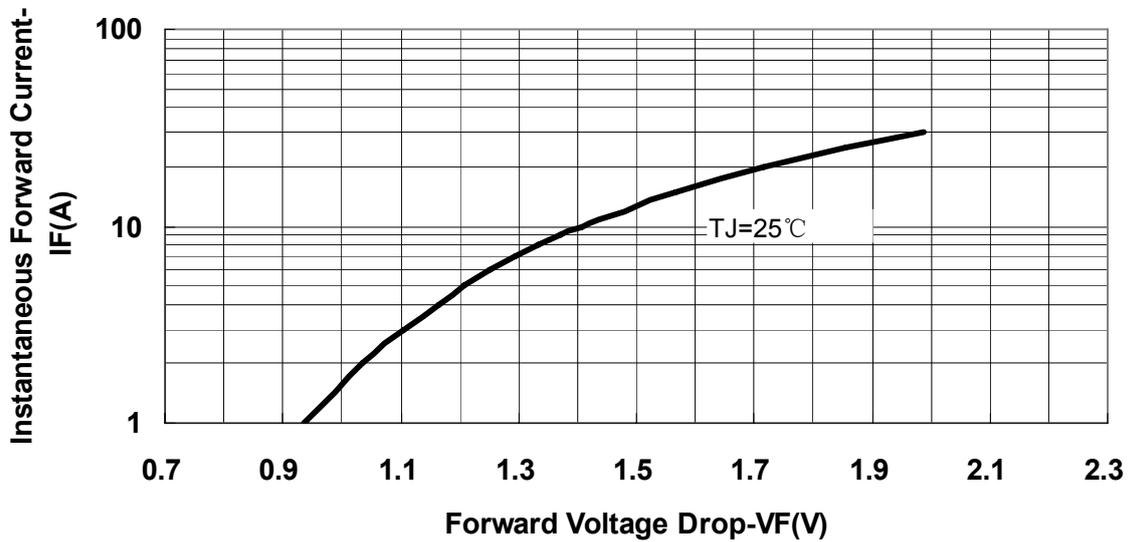


Fig.3-Typical Forward Voltage Drop Characteristics

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